



2811

## PATENT

Case Docket No. MICRON.00901

Date: July 23, 2001

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In re application of : Schuegraf et al.  
App. No. : 08/932,228  
Filed : September 17, 1997  
For : SHALLOW TRENCH  
ISOLATION USING LOW  
DIELECTRIC CONSTANT  
INSULATOR  
Examiner : Hung Vu  
Art Unit : 2811

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on

July 23, 2001

(Date)

Adeel S. Akhtar, Reg. No. 41,394

**ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231**

Sir:

Transmitted herewith is an amendment in the above-identified application.

(X) A Request for Reconsideration in 5 pages.  
(X) Please charge any additional fees, including any fees for additional extension of time, or credit overpayment to Deposit Account No. 11-1410.  
(X) Return prepaid postcard.

Adeel S. Akhtar  
Registration No. 41,394  
Attorney of Record



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant	:	Schuegraf et al.	)	Group Art Unit 2811
Appl. No.	:	08/932,228	)	
Filed	:	September 17, 1997	)	
For	:	SHALLOW TRENCH ISOLATION USING LOW DIELECTRIC CONSTANT INSULATOR	)	
Examiner	:	Hung Vu	)	

*#22  
Req for  
Reconsideration  
F Jones  
8-1-01*

**REQUEST FOR RECONSIDERATION**

Assistant Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

In response to the Final Office Action, mailed June 5, 2001, Applicants respectfully request reconsideration of the application in view of the comments below.

**REMARKS**

The Examiner has continued to reject the claims in view of prior art. Applicants respectfully traverse the rejections and submit that the Examiner is unjustifiably ignoring claim language.

**Rejections Under 35 U.S.C. Section 102 (a)**

The Examiner has rejected Claims 21, 22 and 24 as being anticipated by Anjum et al. (U.S. Patent No. 5,372,951). Anjum et al. taught formation of a halide-doped silicon oxide by a thermal oxidation process, or a LoCal Oxidation of Silicon (LOCOS) process. Consequently, the final structure of Anjum et al. is readily recognized as a product of such a process due to the characteristic bird's beak structure inevitably produced by the process of Anjum et al. *See Figure 5 of Anjum et al.*